

(19) World Intellectual Property Organization
International Bureau



(43) International Publication Date
20 March 2008 (20.03.2008)

PCT

(10) International Publication Number
WO 2008/031742 A3

(51) International Patent Classification:

C03C 3/06 (2006.01) *C03C 4/20* (2006.01)
C03B 20/00 (2006.01)

(21) International Application Number:

PCT/EP2007/059217

(22) International Filing Date:

4 September 2007 (04.09.2007)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data:

10 2006 043 738.1

13 September 2006 (13.09.2006) DE

(71) Applicants (for all designated States except US): **HER-AEUS QUARZGLAS GMBH & CO. KG** [DE/DE]; Quarzstrasse 8, 63450 Hanau (DE). **SHIN-ETSU QUARTZ PRODUCTS CO., LTD.** [JP/JP]; 22-2, Nishi-Shinjuku 1-chome, Shinjuku-ku, Tokyo, Tokyo 160-0023 (JP).

(72) Inventors; and

(75) Inventors/Applicants (for US only): **WEBER, Juergen** [DE/DE]; Hellbuehrling 6, 63801 Kleinos-theim (DE). **SATO, Tatsuhiro** [JP/JP]; 2-46-202,

Hideyama, Azumi-machi, Koriyama-shi, Fukushima, Fukushima 963-0101 (JP). **SCHNEIDER, Ralf** [DE/DE]; Kaethe-Kollwitz-Ring 74, 63486 Bruchkoebel (DE). **HOFMANN, Achim** [DE/DE]; Steinhausenstrasse 17, 60599 Frankfurt (DE). **GEBAUER, Christian** [DE/JP]; Fukasawa 6-2-12, Setagaya-ku, Tokyo, Tokyo 158-0081 (JP).

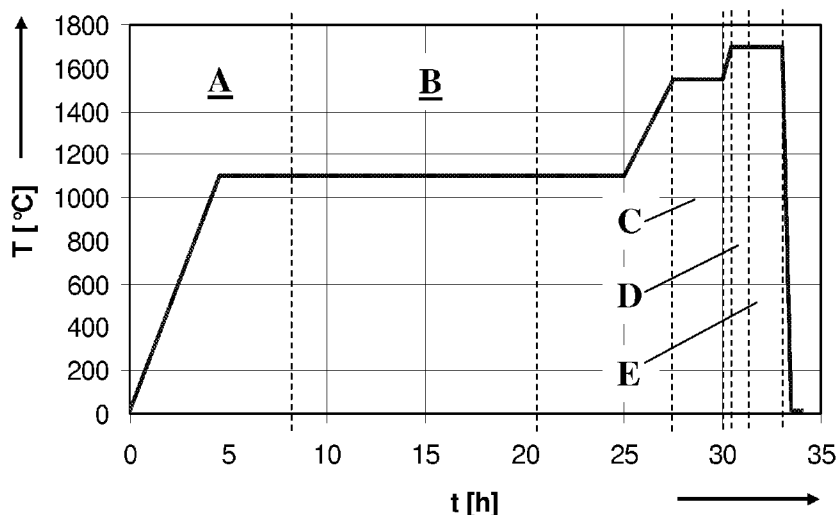
(74) Agent: **STAUDT, Armin**; Auf der Mauer 8, 63674 Altenstadt (DE).

(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM,

[Continued on next page]

(54) Title: COMPONENT OF QUARTZ GLASS FOR USE IN SEMICONDUCTOR MANUFACTURE AND METHOD FOR PRODUCING THE SAME



(57) Abstract: The invention starts from a known component of quartz glass for use in semiconductor manufacture, which component at least in a near-surface region shows a co-doping of a first dopant and of a second oxidic dopant, said second dopant containing one or more rare-earth metals in a concentration of 0.1-3% by wt. each (based on the total mass of SiO₂ and dopant). Starting from this, to provide a quartz glass component for use in semiconductor manufacture in an environment with etching action, which component is distinguished by both high purity and high resistance to dry etching and avoids known drawbacks caused by co-doping with aluminum oxide, it is suggested according to the invention that the first dopant should be nitrogen and that the mean content of metastable hydroxyl groups of the quartz glass is less than 30 wtppm.



ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM),
European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI,
FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, MT, NL, PL,
PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM,
GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

— *before the expiration of the time limit for amending the
claims and to be republished in the event of receipt of
amendments*

Published:

— *with international search report*

(88) Date of publication of the international search report:

22 May 2008